

Cont'd
E1 wherein the stoichiometry of said BST high dielectric thin film material is substantially uniform at least at both sidewall regions.

Sub F3
E2 48. (Fourth Amended) A capacitor comprising:

a material layer having a first level and a second level, said first and second levels being connected by at least two sidewall regions between said first and second levels; and

a post deposition doped BST high dielectric constant thin film material formed at least on both sidewall regions;

wherein the stoichiometry of said BST high dielectric thin film material is substantially uniform at least at both sidewall regions; and

a capping layer provided over at least a portion of said BST thin film material.

Sub F5
E3 74. (Fourth Amended) An integrated circuit capacitor device comprising:

a material layer having a first level and a second level, said first and second levels being connected by at least two sidewall regions between said first and second levels; and

a post deposition doped BST high dielectric constant thin film material formed at least on both sidewall regions;

wherein the stoichiometry of said BST high dielectric thin film material is substantially uniform at least at both sidewall regions; and

a second electrode provided on said BST high dielectric thin film layer.